

ABSTRACT OF THE DISCLOSURE

The semiconductor light emitting device includes a semiconductor substrate formed from InP, an active layer, an n-type cladding layer formed from InGaAsP, and a p-type cladding layer formed from InP.

5 The active layer is formed at the upper side of the semiconductor substrate. The n-type cladding layer and the p-type cladding layer are formed so as to hold the active layer therebetween. The semiconductor light emitting device is, given that, a refractive index of

10 the n-type cladding layer is  $n_a$ , and a refractive index of the p-type cladding layer is  $n_b$ , set so as to be the relationship of  $n_a > n_b$  in which the refractive index  $n_a$  of the n-type cladding layer is higher than the

15 refractive index  $n_b$  of the p-type cladding layer, and due to the distribution of light generated by the active layer being deflected to the n-type cladding layer side, optical loss by intervalence band light absorption at the p-type cladding layer is suppressed,

20 and high-power light output can be obtained.